## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number		
D2337 D2	Unassigned		
Applicant(s) Fwu-Iuan Hshieh et al.			
Filing Date	Group Art Unit		
Filed Herewith	2818		

	U.S.	PAT	ENT	DOCU	MENT:
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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
OK	1	6,144,065	11/7/2000	Kinzer	257	327	
CX	2	6,025,237	2/15/2000	Choi	438	301	graph (S. S. Saldanian )
O	3	5,072,266	12/10/1991	Bulucea et al.	357	23.4	
CX	4	4,971,929	11/20/90	D'Anna et al.	437	192	
X	5	5,770,514	06/23/1998	Matsuda et al.	438	589	
OX	6	5,567,634	10-1996	Hebert et al.	437	41	
OK	7 🗻	6,125,149 6,215,149	04-2001	Lee et al.	257	328	
OX	8	6,225,649	05-2001	Minato	257	133	
O	9	5,541,425	07/30/1996	Nishihara	257	139	
OK	10	5,468,982	11/21/1995	Hshieh et al.	257	331	
CX	11	5,866,931	02/02/1999	Bulucea et al.	257	331	

## FOREIGN PATENT DOCUMENTS

	REF	REF DOCUMENT NUMBER DATE	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OK	1	WO 94/03922	02/17/1994	PCT	H01L 21	265	>	
OX	2	61190981	08/25/1986	JP	H01L 29	78		1
CN	3	DE 19507146A1	11/1/1996	Germany	H01L 29	78		1
			o		:			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OK	1	Matsumoto, S. et al., "A 70-V, 90-ma-mm*, High-Speed Double-Layer Gate UMOSFET Realized by Selective CVD Tungsten, Proceedings of the 6th International Symposium on Power Semiconductor Deives & IC's, Switzerland, May 31-JUne 2, 1994, pgs. 365-369.

EXAMINER ( Livety Kovacek

DATE CONSIDERED

3/21/04

EXAMINER: Initial if citation of misidered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.